CSD18512Q5B 40 V N-channel NexFET™ power MOSFET

1 Features

- Low $R_{DS(ON)}$
- Low thermal resistance
- Avalanche rated
- Logic level
- Pb-free terminal plating
- RoHS compliant
- Halogen-free
- SON 5 mm × 6 mm plastic package

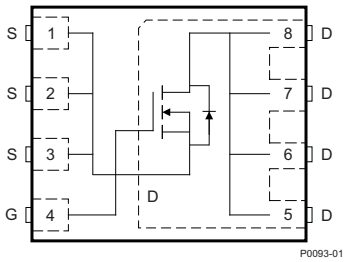
2 Applications

- DC-DC conversion
- Secondary side synchronous rectifier
- Motor control

3 Description

This 40 V, 1.3 mΩ, 5 mm × 6 mm NexFET™ power MOSFET is designed to minimize losses in power conversion applications.

Top View



Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain to source voltage	40		V
Q_g	Gate charge total (10 V)	75		nC
Q_{gd}	Gate charge gate to drain	13.3		nC
$R_{DS(on)}$	Drain to source on resistance	V_{GS} = 4.5 V	1.8	mΩ
		V_{GS} = 10 V	1.3	mΩ
$V_{GS(th)}$	Threshold voltage	1.6		V

Ordering Information(1)

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD18512Q5B	2500	13-Inch Reel	SON 5 mm × 6 mm Plastic Package	Tape and Reel
CSD18512Q5BT	250	7-Inch Reel		

(1) For all available packages, see the orderable addendum at the end of the datasheet.

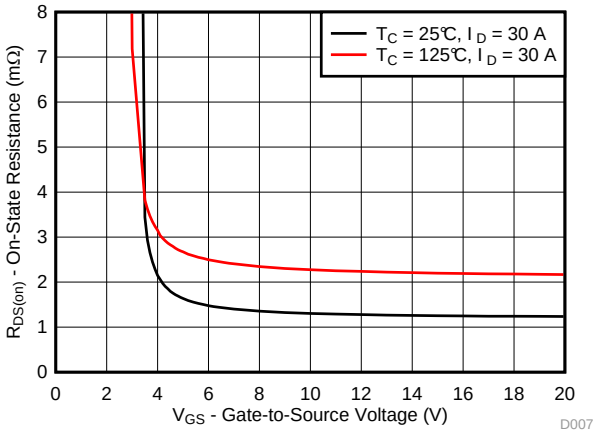
Absolute Maximum Ratings

T_A = 25°C		VALUE	UNIT
V_{DS}	Drain to source voltage	40	V
V_{GS}	Gate to source voltage	±20	V
I_D	Continuous drain current (package limited)	100	A
	Continuous drain current (silicon limited), T_C = 25°C	211	
	Continuous drain current(1)	32	
I_{DM}	Pulsed drain current(2)	400	A
P_D	Power dissipation(1)	3.1	W
	Power dissipation, T_C = 25°C	139	
T_J, T_{stg}	Operating Junction, Storage Temperature	–55 to 150	°C
E_{AS}	Avalanche energy, single pulse I_D = 64 A, L = 0.1 mH, R_G = 25 Ω	205	mJ

(1) Typical $R_{\theta JA}$ = 40°C/W on a 1 inch^2 , 2 oz. Cu pad on a 0.06 inch thick FR4 PCB.

(2) Max $R_{\theta JC}$ = 0.9°C/W, pulse duration ≤100 µs, duty cycle ≤1%

$R_{DS(on)}$ vs V_{GS}



Gate Charge

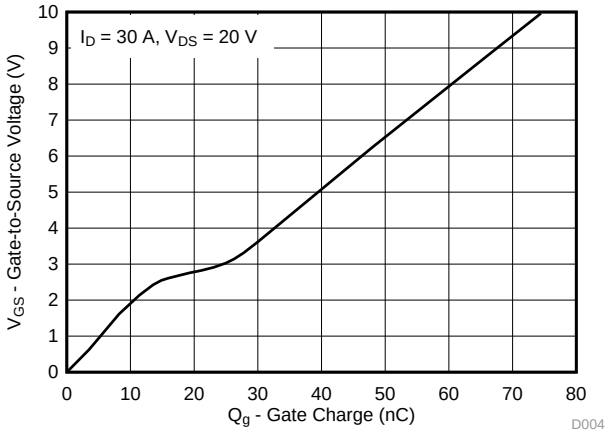


Table of Contents

4 Revision History

Changes from Original (December 2016) to Revision A	Page
• Corrected the SOA in Figure 10	5

5 Specifications

5.1 Electrical Characteristics

(T_A = 25°C unless otherwise stated)

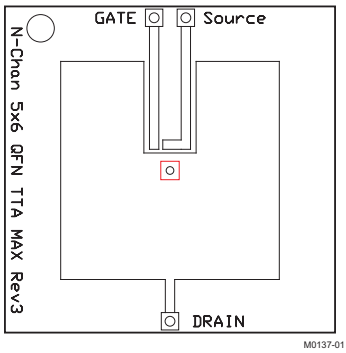
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain to source voltage	V_{GS} = 0 V, I_D = 250 μA	40			V
I_{DSS}	Drain to source leakage current	V_{GS} = 0 V, V_{DS} = 32 V			1	μA
I_{GSS}	Gate to source leakage current	V_{DS} = 0 V, V_{GS} = 20 V			100	nA
$V_{GS(th)}$	Gate to source threshold voltage	V_{DS} = V_{GS}, I_D = 250 μA	1.3	1.6	2.2	V
$R_{DS(on)}$	Drain to source on resistance	V_{GS} = 4.5 V, I_D = 30 A		1.8	2.3	mΩ
		V_{GS} = 10 V, I_D = 30 A		1.3	1.6	mΩ
g_{fs}	Transconductance	V_{DS} = 20 V, I_D = 30 A		136		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input capacitance	V_{GS} = 0 V, V_{DS} = 20 V, f = 1 MHz		5480	7120	pF
C_{oss}	Output capacitance			537	699	pF
C_{rss}	Reverse transfer capacitance			256	333	pF
R_G	Series gate resistance			1.0	2.0	Ω
Q_g	Gate charge total (4.5 V)	V_{DS} = 20 V, I_D = 30 A		37	48	nC
Q_g	Gate charge total (10 V)			75	98	nC
Q_{gd}	Gate charge gate to drain			13.3		nC
Q_{gs}	Gate charge gate to source			15.1		nC
$Q_{g(th)}$	Gate charge at V_{th}			8.2		nC
Q_{oss}	Output charge	V_{DS} = 20 V, V_{GS} = 0 V		23		nC
$t_{d(on)}$	Turn on delay time	V_{DS} = 20 V, V_{GS} = 10 V, I_{DS} = 30 A, R_G = 0 Ω		7		ns
t_r	Rise time			16		ns
$t_{d(off)}$	Turn off delay time			31		ns
t_f	Fall time			7		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	I_{SD} = 30 A, V_{GS} = 0 V		0.75	1.0	V
Q_{rr}	Reverse recovery charge	V_{DS}= 20 V, I_F = 30 A, di/dt = 300 A/μs		22		nC
t_{rr}	Reverse recovery time			17		ns

5.2 Thermal Information

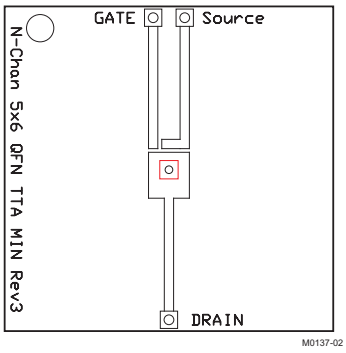
(T_A = 25°C unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case (top of package) thermal resistance (1)			0.9	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance (1) (2)			50	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1 inch^2 (6.45 cm^2), 2 oz. (0.071 mm thick) Cu pad on a 1.5 inch × 1.5 inch (3.81 cm × 3.81 cm), 0.06 inch (1.52 mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.
(2) Device mounted on FR4 material with 1 inch^2 (6.45 cm^2), 2 oz. (0.071 mm thick) Cu.



Max $R_{\theta JA}$ = 50°C/W when mounted on 1 inch^2 (6.45 cm^2) of 2 oz. (0.071 mm thick) Cu.



Max $R_{\theta JA}$ = 125°C/W when mounted on a minimum pad area of 2 oz. (0.071 mm thick) Cu.

5.3 Typical MOSFET Characteristics

T_A = 25°C (unless otherwise stated)

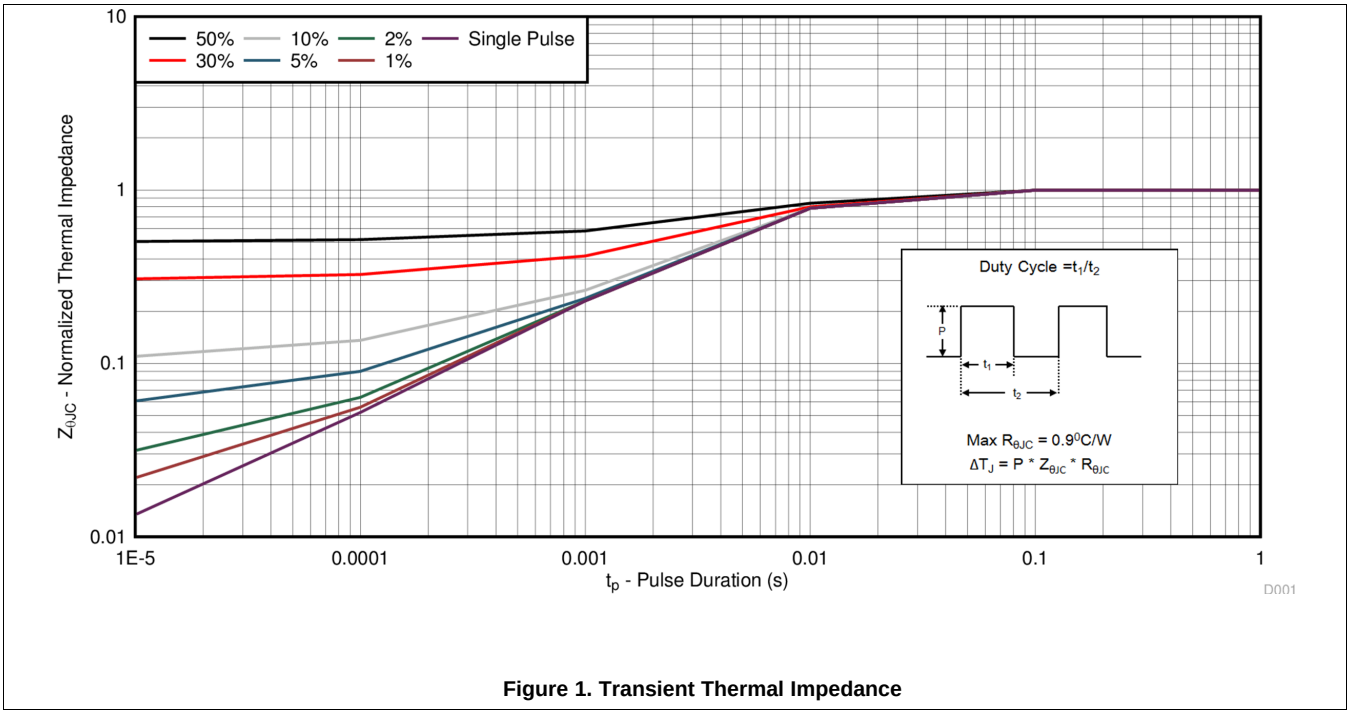


Figure 1. Transient Thermal Impedance

Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)

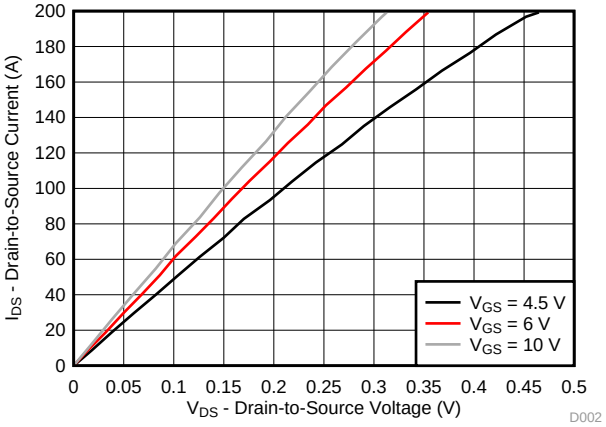


Figure 2. Saturation Characteristics

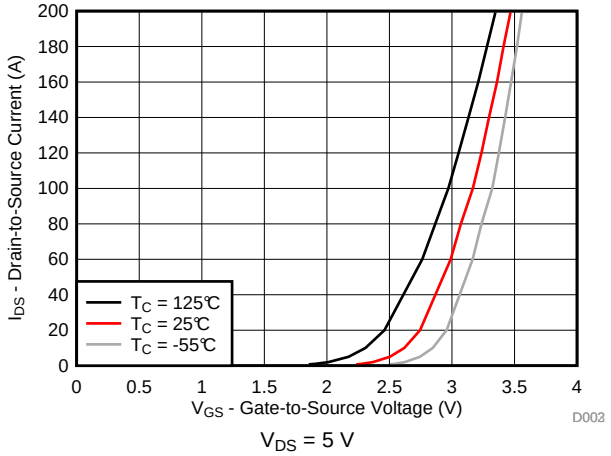


Figure 3. Transfer Characteristics

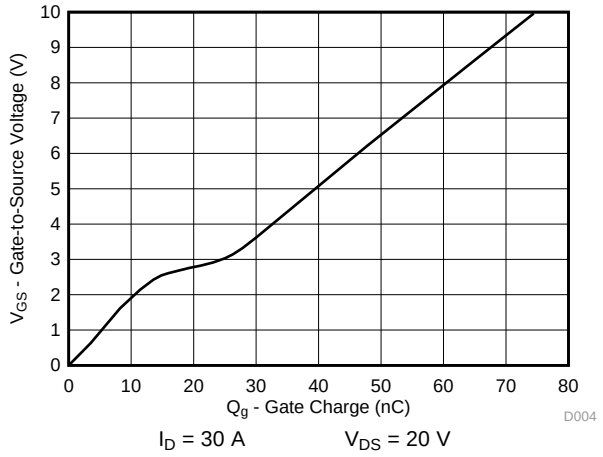


Figure 4. Gate Charge

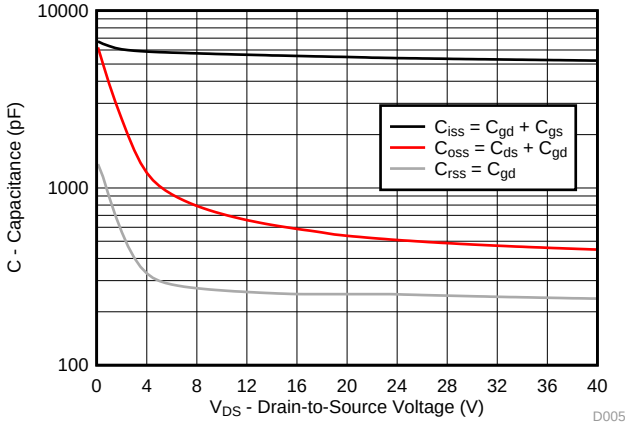


Figure 5. Capacitance

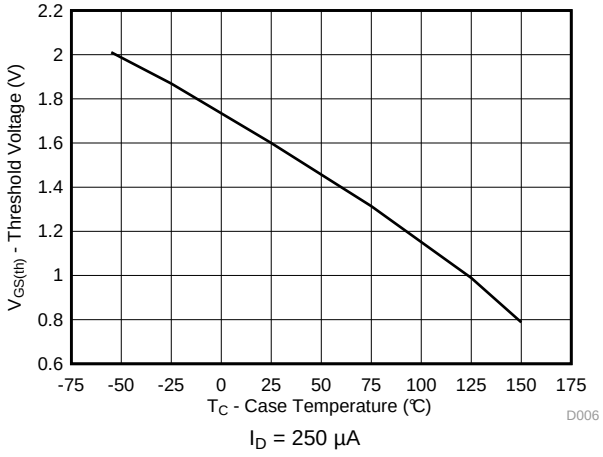


Figure 6. Threshold Voltage vs Temperature

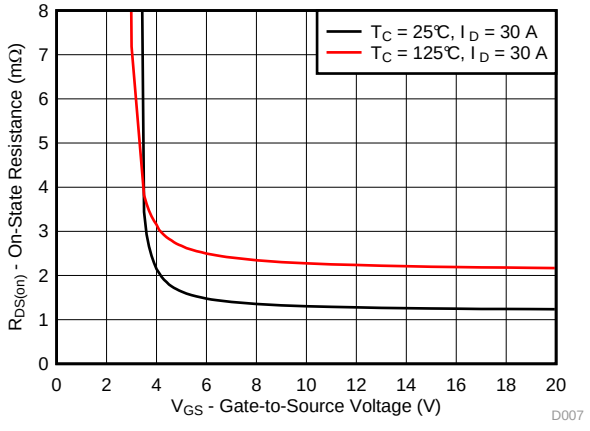


Figure 7. On-State Resistance vs Gate-to-Source Voltage

Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)

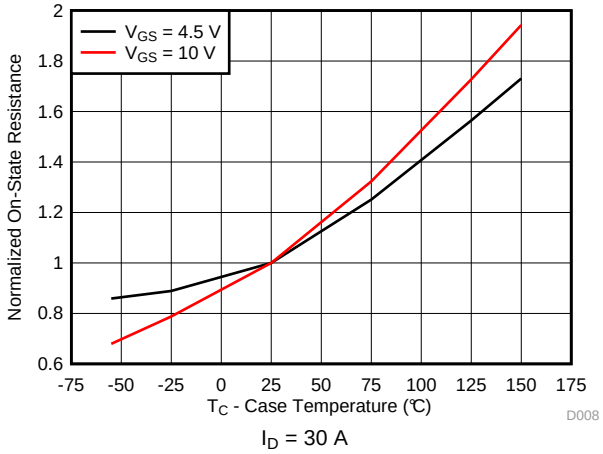


Figure 8. Normalized On-State Resistance vs Temperature

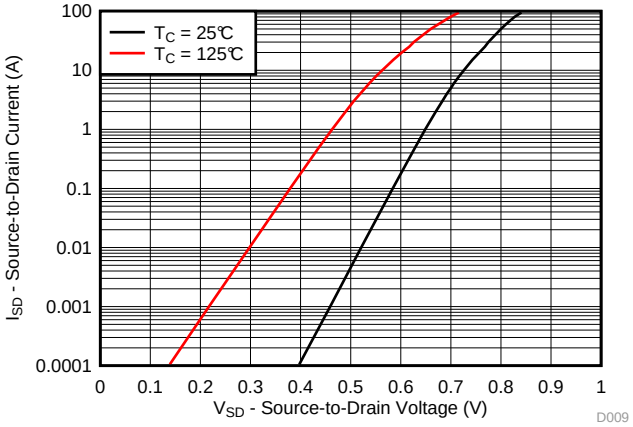


Figure 9. Typical Diode Forward Voltage

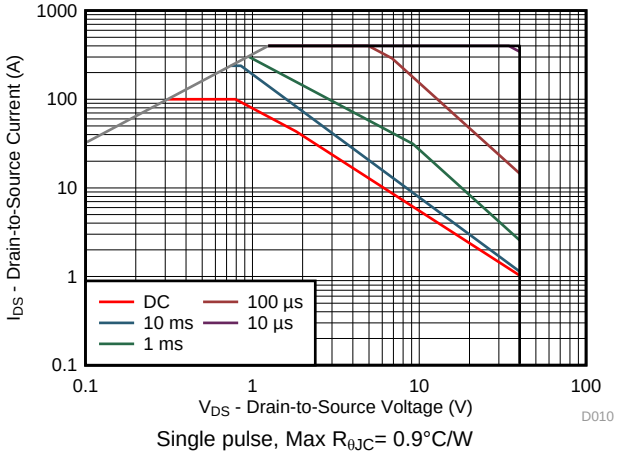


Figure 10. Maximum Safe Operating Area

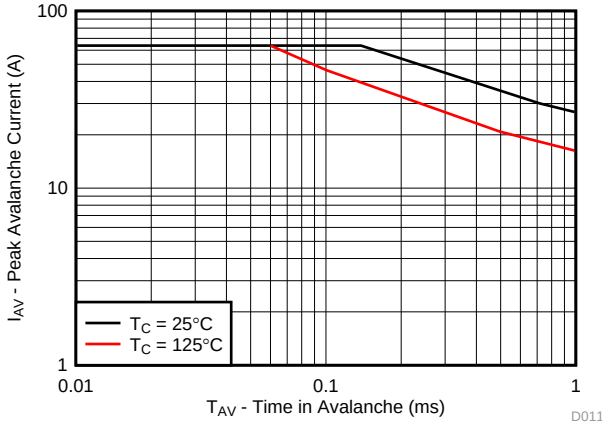


Figure 11. Single Pulse Unclamped Inductive Switching

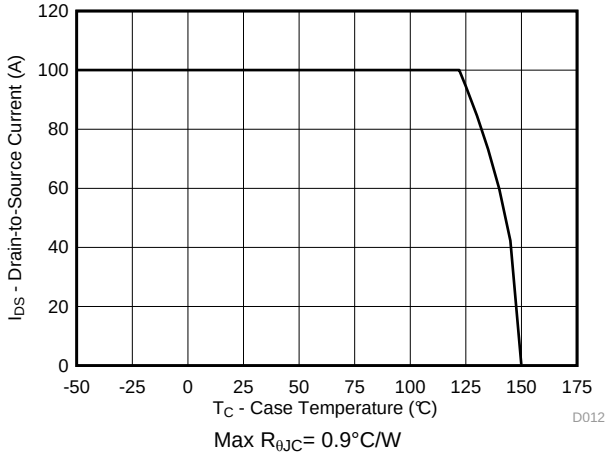


Figure 12. Maximum Drain Current vs Temperature

6 Device and Documentation Support

6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community ***TI's Engineer-to-Engineer (E2E) Community.*** Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.2 Trademarks

NexFET, E2E are trademarks of Texas Instruments.
All other trademarks are the property of their respective owners.

6.3 Electrostatic Discharge Caution

These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

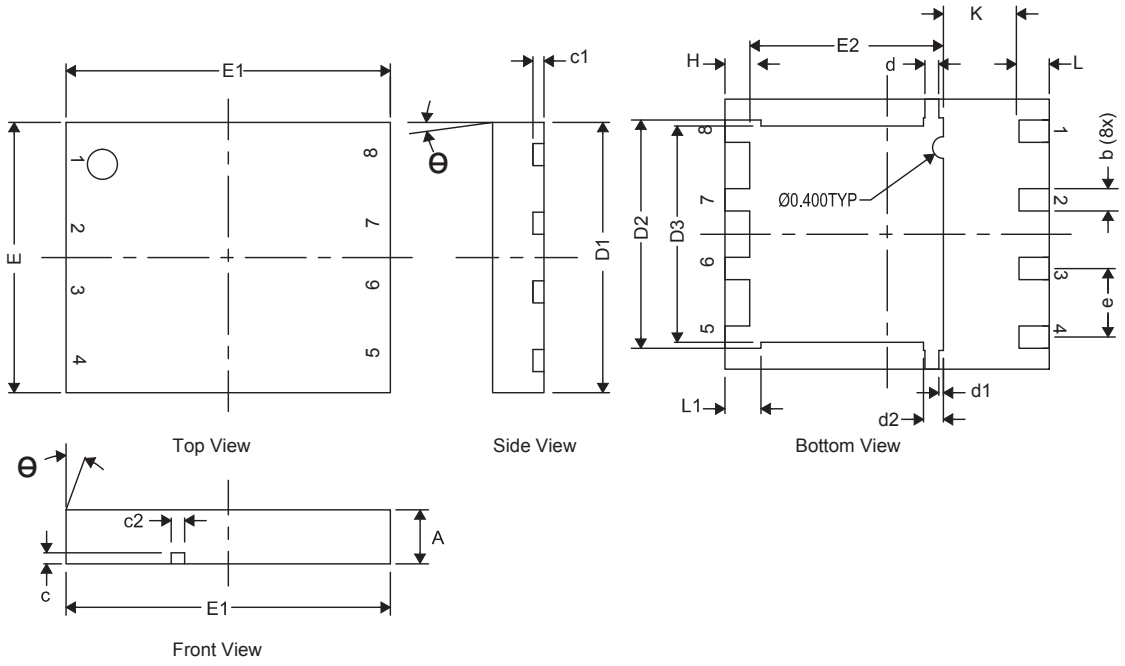
6.4 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

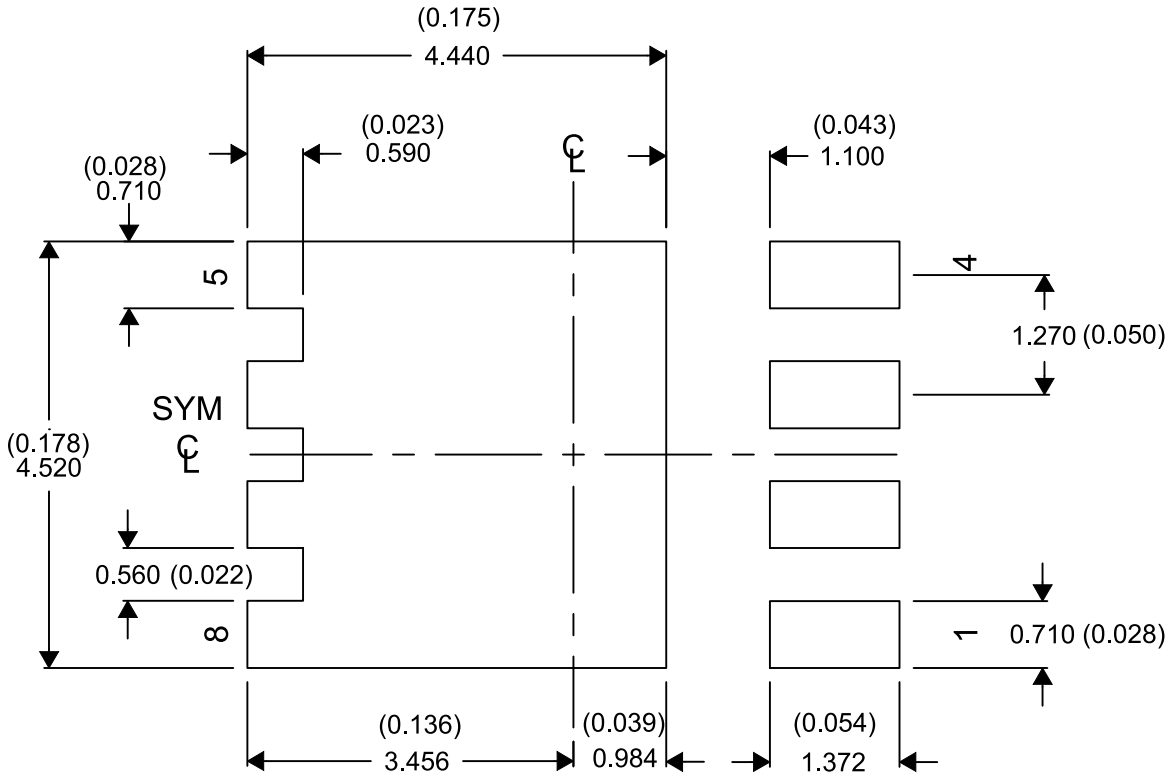
7 Mechanical, Packaging, and Orderable Information

7.1 Q5B Package Dimensions



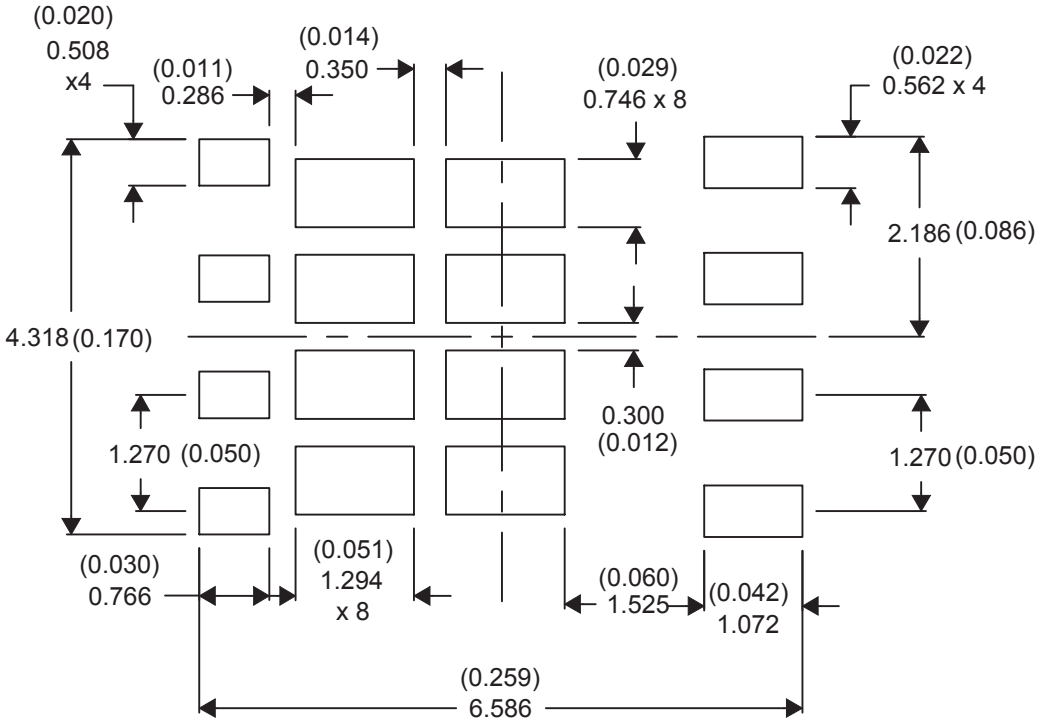
DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.80	1.00	1.05
b	0.36	0.41	0.46
c	0.15	0.20	0.25
c1	0.15	0.20	0.25
c2	0.20	0.25	0.30
D1	4.90	5.00	5.10
D2	4.12	4.22	4.32
D3	3.90	4.00	4.10
d	0.20	0.25	0.30
d1	0.085 TYP		
d2	0.319	0.369	0.419
E	4.90	5.00	5.10
E1	5.90	6.00	6.10
E2	3.48	3.58	3.68
e	1.27 TYP		
H	0.36	0.46	0.56
L	0.46	0.56	0.66
L1	0.57	0.67	0.77
θ	0°	-	-
K	1.40 TYP		

7.2 Recommended PCB Pattern

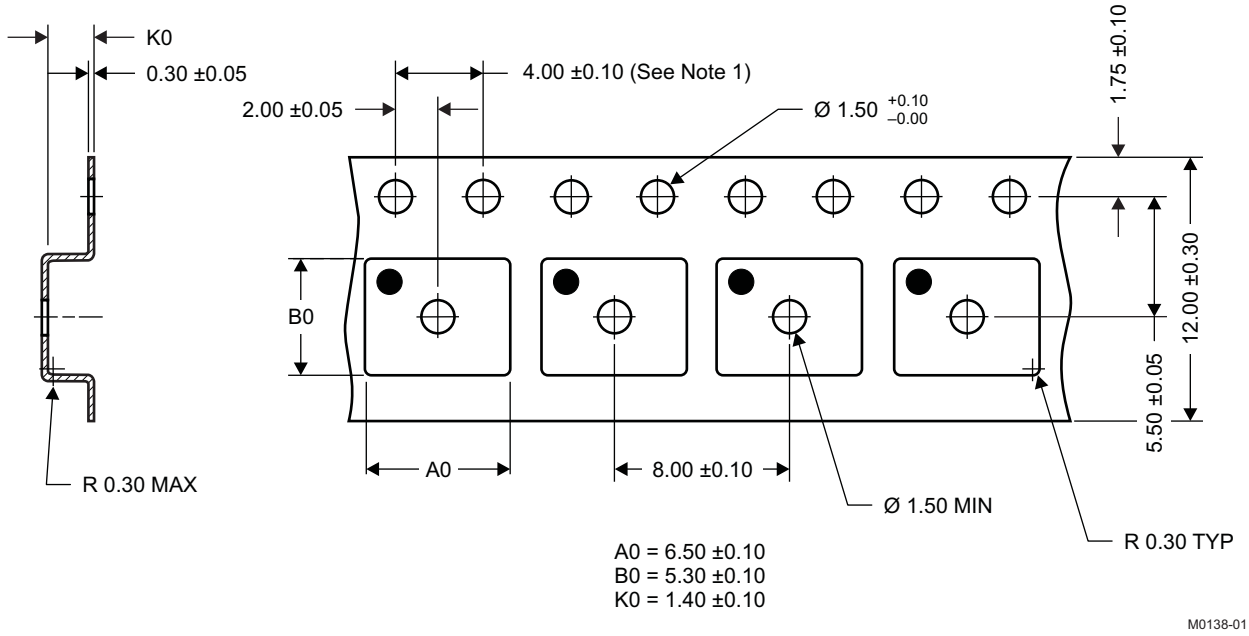


For recommended circuit layout for PCB designs, see application note SLPA005 – *Reducing Ringing Through PCB Layout Techniques*.

7.3 Recommended Stencil Pattern



7.4 Q5B Tape and Reel Information



Notes:

1. 10-sprocket hole-pitch cumulative tolerance ±0.2.
2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm.
3. Material: black static-dissipative polystyrene.
4. All dimensions are in mm (unless otherwise specified).
5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD18512Q5B	Active	Production	VSON-CLIP (DNK) | 8	2500 | LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18512
CSD18512Q5B.B	Active	Production	VSON-CLIP (DNK) | 8	2500 | LARGE T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18512
CSD18512Q5BT	Active	Production	VSON-CLIP (DNK) | 8	250 | SMALL T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18512
CSD18512Q5BT.B	Active	Production	VSON-CLIP (DNK) | 8	250 | SMALL T&R	ROHS Exempt	NIPDAU	Level-1-260C-UNLIM	-55 to 150	CSD18512

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

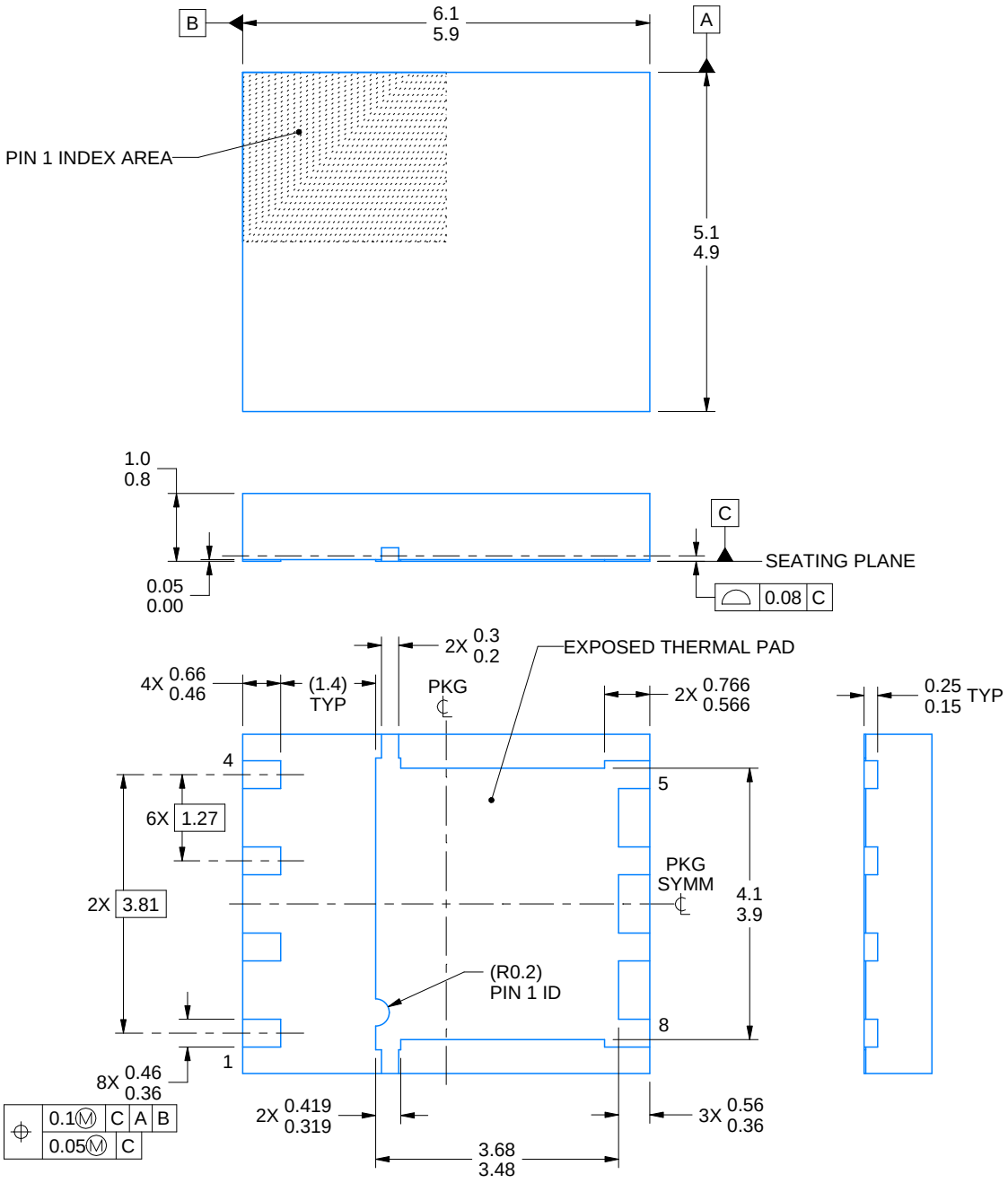
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

PACKAGE OUTLINE

DNK0008A

VSON-CLIP - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



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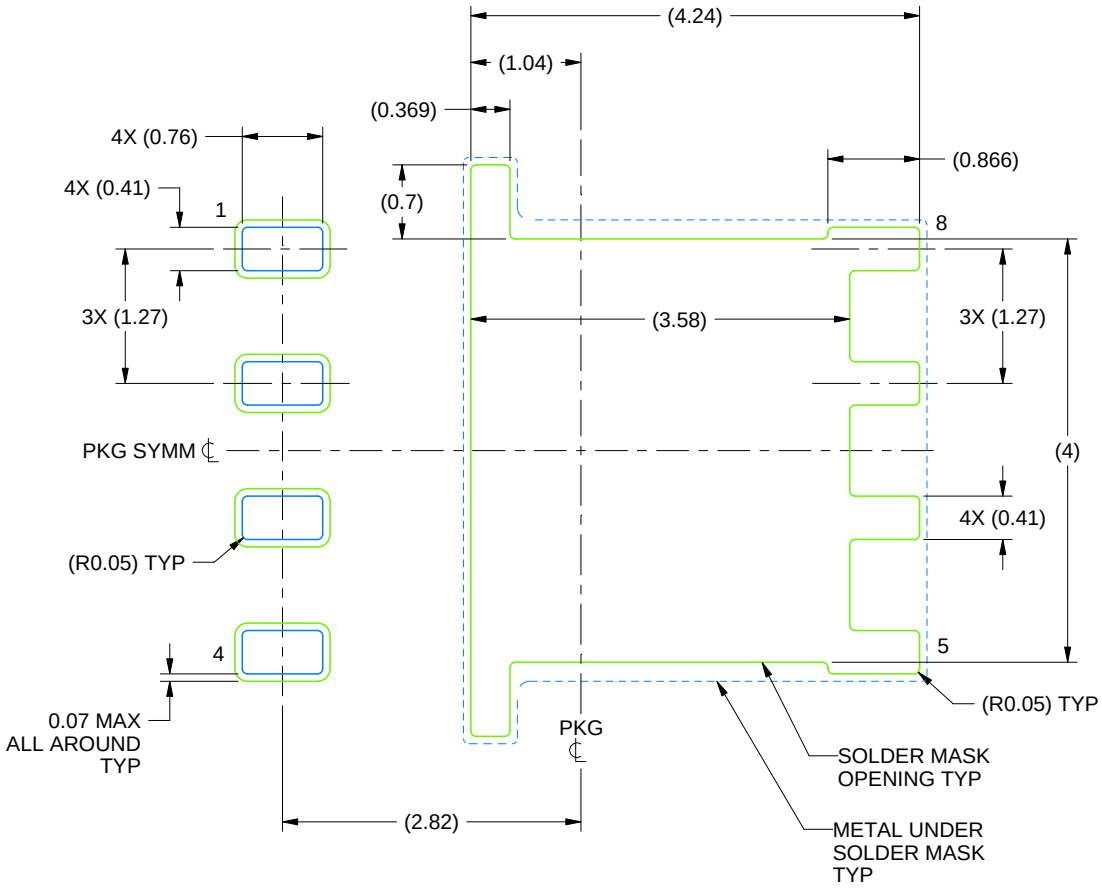
NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE: 14X

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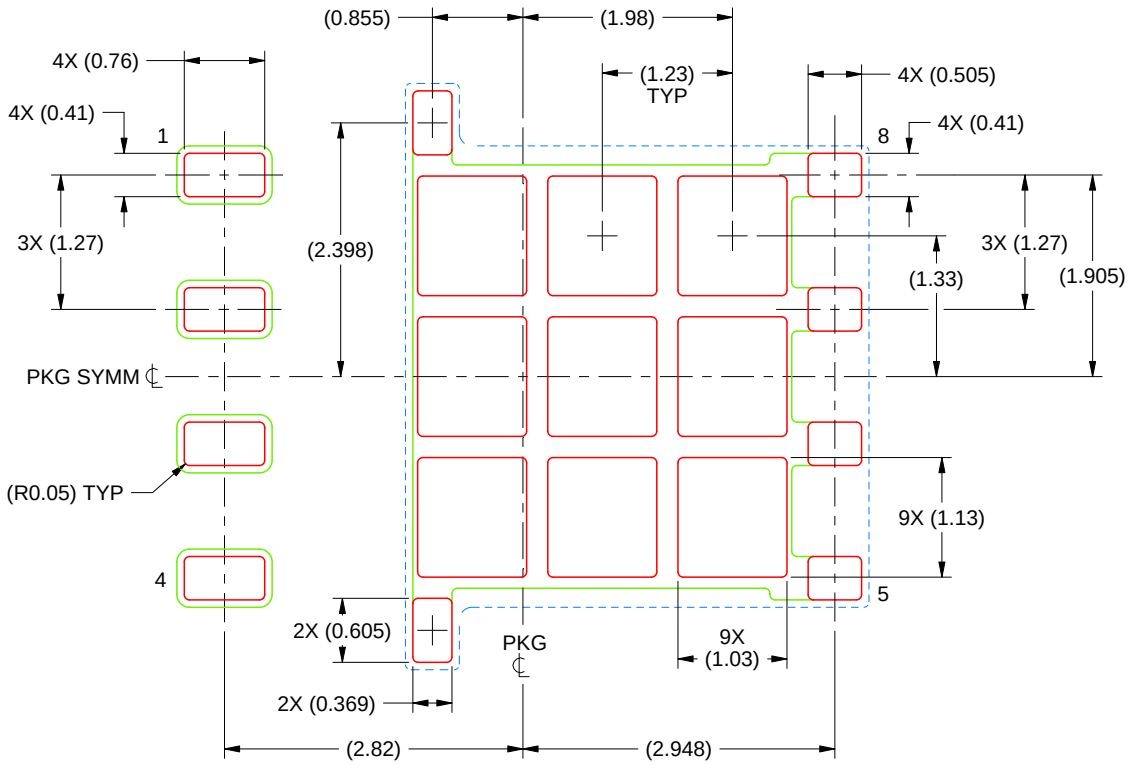
NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 14X

74% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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